

U.S. Application No. 10/067,486

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AMENDMENTS TO THE ABSTRACT:

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A semiconductor substrate ~~comprises~~ includes a porous semiconductor having: a porous layer, with an impurity concentration distribution varying in the depth direction, or. ~~Alternatively, the semiconductor substrate comprises a porous layer comprising having~~ a porous semiconductor containing an impurity with a content of $1 \times 10^{18} \text{ cm}^{-3}$ or more, or comprises a porous layer provided by pore formation in an epitaxial growth layer. A thin film semiconductive member is formed on one surface of a supporting substrate with a porous layer provided having the above mentioned configuration therebetween, and separated from the supporting substrate by cleavage in the porous layer. In a A method for of making a semiconductor substrate, includes forming a variant impurity layer with an impurity concentration varying in the depth direction is formed on one surface of a supporting substrate, and converting. Next, the variant impurity layer is converted into a porous layer having a variant porosity in the depth direction. In a A method for of making a thin-film semiconductive member, includes forming a semiconductive thin film is formed and is separated from on the supporting substrate and separating it by cleavage in the porous phase, in addition to the method for making the semiconductor substrate.